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APPLICATION NUMBER	FILING DATE	FIRST NAMED APPLICANT	ATTY, DOCKET NO.	
08/578.980 12/2 7/9 5 KAMAKURA			т	39-5461-0
				EXAMINER
		B5M1/0415		
OBLON SPIVAK MCCLELLAND MAIER & NEUSTADT			WILLE V	
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1755 JEFFERSON DAVIS HIGHWAY				0
ARLINGTON VA 22202			2508	
			DATE MAILED); 04/15/97

This is a communication from the examiner in charge of your application. COMMISSIONER OF PATENTS AND TRADEMARKS

OFFICE ACTION SUMMARY				
Responsive to communication(s) filed on	· · · · · · · · · · · · · · · · · · ·			
This action is FINAL.				
Since this application is in condition for allowance except for accordance with the practice under Ex parte Quayle, 1935 D	formal matters, prosecution as to the merits is closed in .C. 11; 453 O.G. 213.			
A shortened statutory period for response to this action is set to a whichever is longer, from the mailing date of this communication. the application to become abandoned. (35 U.S.C. § 133). Extendible 1.136(a).	Failure to respond within the period for response will cause			
Disposition of Claims				
[] Claim(s)	is/are pending in the application.			
Claim(s) / -/O	is/are peruning in the applicationis/are withdrawn from consideration.			
	is/are allowed.			
Claim(s)	is/are rejected.			
Claim(s)	is/are objected to.			
Claim(s)	are subject to restriction or election requirement.			
See the attached Notice of Draftsperson's Patent Drawing Relation The drawing(s) filed on The proposed drawing correction, filed on The specification is objected to by the Examiner. The oath or declaration is objected to by the Examiner.	is/are objected to by the Examiner.			
Priority under 35 U.S.C. § 119				
Acknowledgment is made of a claim for foreign priority under	· 35 U.S.C. § 119(a)-(d).			
☐ All ☐ Some* ☐ None of the CERTIFIED copies or	f the priority documents have been			
received. received in Application No. (Series Code/Serial Number) received in this national stage application from the Intern				
*Certified copies not received:				
Acknowledgment is made of a claim for domestic priority und	ter 35 U.S.C. § 119(e).			
Attachment(s)				
Notice of Reference Cited, PTO-892	08/578980			
☐ Information Disclosure Statement(s), PTO-1449, Paper No(s	08/5			
Interview Summary, PTO-413	r			
Ξ .				
Notice of Draftperson's Patent Drawing Review, PTO-948	•			
Notice of Informal Patent Application, PTO-152				

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DETAILED ACTION

Claim Rejections - 35 USC § 112

- 1. Claims 8, 9, and 10 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- 2. Claims 8, 9, and 10 refer to a dense layer. This term is not defined and does not correspond to the usual meaning of dense. These claims also refer to the lattice constant as being 10⁻². This is not understood since a lattice constant should have dimensions and second, it is in a range which is not physical, no matter what the dimensions.

Claim Rejections - 35 USC § 102

3. Claims 1 and 3 are rejected under 35 U.S.C. 102(b) as being anticipated by Scifres et al. See previous Office Action for a discussion of this rejection.

Claim Rejections - 35 USC § 103

- 4. Claims 2 and 8, 9, and 10, as far as they are understood, are rejected under 35 U.S.C. 103(a) as being unpatentable over Scifres et al in view of Inoue et al.
- 5. For a discussion of claim 2 rejection see the previous Office Action. With respect to claims 8, 9, and 10, Scifres et al discusses the basic device structure and refers to the strain layer



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thickness as being approximately 10 nm(column 4, line 47). Scifres et al also discusses the lattice mismatch as being less than or equal to 4%. Inoue et al discusses the defect density as being in the range of 10⁶/cm² which corresponds to a value greater than 10⁴/cm³. It would have been obvious to provide the Scifres et al device with the defect density taught by Inoue et al to improve the defect protection.

- 6. Claims 4, 5, and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Scifres et al in view of Sugawara et al. See previous Office Action for a discussion of this rejection.
- 7. Claim 7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Scifres et al in view of Sugawara et al and further in view of Inoue et al. See previous Office Action for a discussion of this rejection.

Response to Arguments

- 8. Applicant's arguments filed 13 January 1997 have been fully considered but they are not persuasive.
- 9. Applicant argues that Scifres et al does not discuss details of defect density, lattice constant or layer thickness. While Scifres et al does not discuss defect density, they do discuss both layer thickness and lattice constant differences as noted above. No discussion of defect density was required before the claims were amended and was therefore not addressed, however, in light of the new claims, it is noted that the question of defect density is addressed by the Inoue et al reference. Applicant also argues that Scifres et al does not show the strain layer as being



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between the electrode and the hetero-configuration, but applicants' attention is drawn to Figure 2 where the strain layer is shown as being in the middle of the buffer layer and there is still a buffer material layer between the strain layer and the hetero-configuration.

- 10. Applicant argues that claims 3, and 4 have features not discussed by Scifres et al. It is noted that Scifres et al teaches a structure where the clad layers are doped for n- and p-type behavior. While Scifres et al does not specify the doping of the active layer, it is standard practice to leave that layer undoped. Thus the features of these claims were properly addressed in the rejection. Applicant also argues that Scifres et al fails to teach the claimed defect layer either in location or material and the defect is not removed by Inoue et al. Applicants' attention is drawn to the discussion above where the location of the defect layer is exactly as shown in the claims and while Scifres et al does not discuss the defect density this is more than made up by the discussion in Inoue et al where the defect density is shown in great detail. Again, all aspects of the claims were discussed in the references provided.
- 11. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).
- 12. A shortened statutory period for response to this final action is set to expire THREE MONTHS from the date of this action. In the event a first response is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period

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action.

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will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event will the statutory period for response expire later than SIX MONTHS from the date of this final

- 13. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas A. Wille whose telephone number is (703) 308-4949.
- 14. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose number is (703) 308-0956.

SARA W. CRANE PRIMARY EXAMINER

GROUP 2500

DAW DLW

April 2, 1997